MITSUBISHI SEMICONDUCTOR < Dual-In-Line Package Intelligent Power Module>

# PS21964-T/-AT/-CT/-TW

TRANSFER-MOLD TYPE INSULATED TYPE

## PS21964-T



#### **INTEGRATED POWER FUNCTIONS**

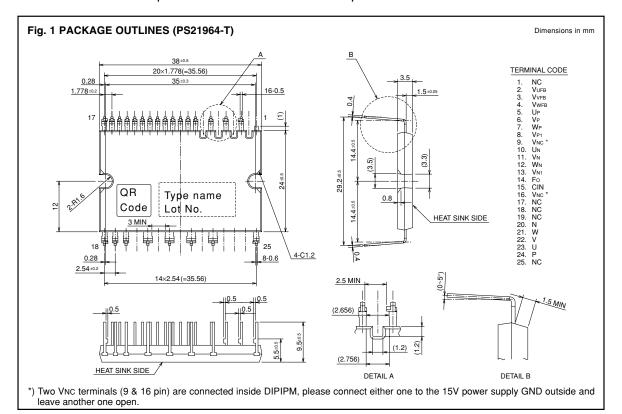
600V/15A low-loss 5<sup>th</sup> generation IGBT inverter bridge for three phase DC-to-AC power conversion

#### INTEGRATED DRIVE, PROTECTION AND SYSTEM CONTROL FUNCTIONS

- For upper-leg IGBTs: Drive circuit, High voltage high-speed level shifting, Control supply under-voltage (UV) protection.
- For lower-leg IGBTs: Drive circuit, Control supply under-voltage protection (UV), Short circuit protection (SC), Over temperature protection (OT).
- Fault signaling: Corresponding to an SC fault (Lower-leg IGBT), a UV fault (Lower-side supply) or an OT fault (LVIC temperature).
- Input interface : 3V, 5V line (High Active).
- UL Approved : Yellow Card No. E80276

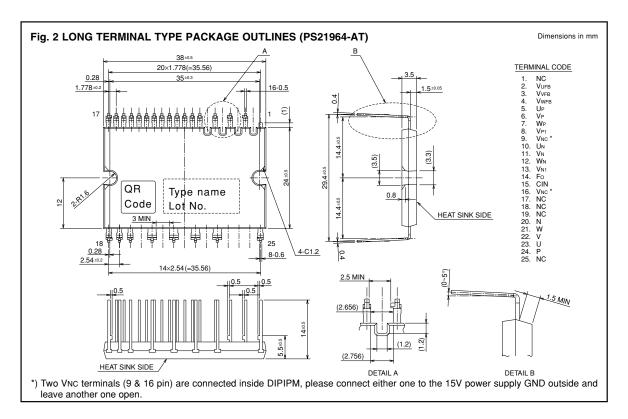
## **APPLICATION**

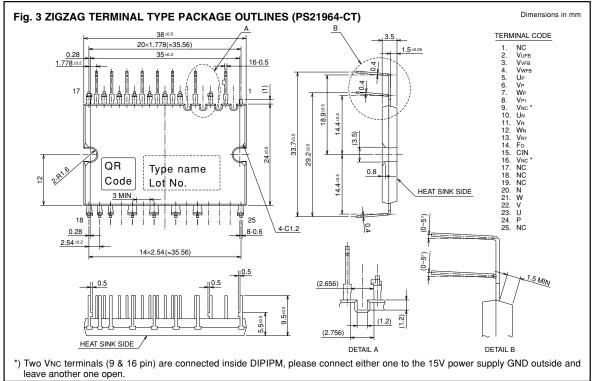
AC100V~200V three-phase inverter drive for small power motor control.





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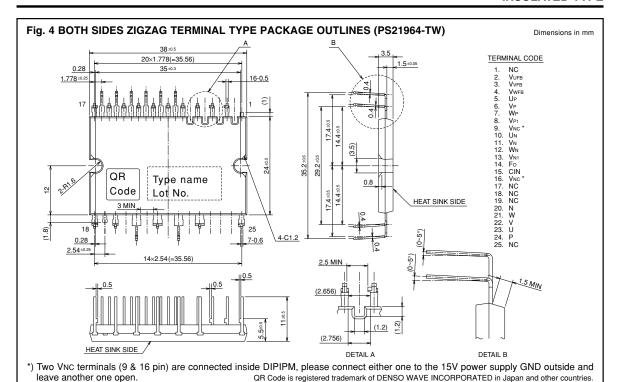


Fig. 5 INTERNAL FUNCTIONS BLOCK DIAGRAM (TYPICAL APPLICATION EXAMPLE) C1 : Electrolytic type with good temperature and frequency characteristics (Note: The capacitance value depends on the PWM control scheme used in the applied system).

C2: 0.22~2µF R-category ceramic capacitor for noise filtering Inrush current limiter circuit DIPIPM AC line input (Note 4) Μ AC line output z TcT L L-side IGBTs Z : Surge absorber C : AC filter (Ceramic capacitor 2.2~6.5nF) Drive (Note : Additionally, an appropriate line-to line surge absorber circuit may become necessar Input sign conditioning depending on the application environment). (Note 6) Fault output (5V line) (15V line) Input logic is high-active. There is a  $3.3k\Omega$  (min) pull-down resistor built-in each input circuit. When using an external CR filter, please make it satisfy the Note1: input threshold voltage.

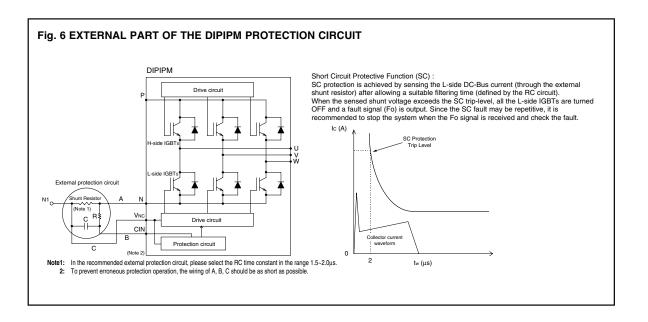
By virtue of integrating an application specific type HVIC inside the module, direct coupling to MCU terminals without any opto-coupler or transformer isolation is possible. (see also Fig. 11)
This output is open drain type. The signal line should be pulled up to the positive side of the 5V power supply with approximately  $10k\Omega$  resistor (see also Fig. 11) The wiring between the power DC link capacitor and the P. N1 terminals should be as short as possible to protect the DIPIPM against catastrophic high



surge voltages. For extra precaution, a small film type snubber capacitor (0.1~0.22µF, high voltage type) is recommended to be mounted close to these P & N1 DC power input pins.

High voltage (600V or more) and fast recovery type (less than 100ns) diodes should be used in the bootstrap circuit. It is recommended to insert a Zener diode (24V/1W) between each pair of control supply terminals to prevent surge destruction. Bootstrap negative electrodes should be connected to U, V, W terminals directly and separated from the main output wires.

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# $\label{eq:maximum ratings} \textbf{MAXIMUM RATINGS} \ (T_j = 25^{\circ}\text{C}, \ unless \ otherwise \ noted) \\ \textbf{INVERTER PART}$

Symbol	Parameter	Condition	Ratings	Unit
Vcc	Supply voltage	Applied between P-N	450	V
VCC(surge)	Supply voltage (surge)	Applied between P-N	500	V
VCES	Collector-emitter voltage		600	V
±IC	Each IGBT collector current	Tc = 25°C	15	Α
±ICP	Each IGBT collector current (peak)	Tc = 25°C, less than 1ms	30	Α
Pc	Collector dissipation	Tc = 25°C, per 1 chip	33.3	W
Tj	Junction temperature	(Note 1)	-20~+125	°C

Note 1: The maximum junction temperature rating of the power chips integrated within the DIPIPM is 150°C (@ Tc ≤ 100°C). However, to ensure safe operation of the DIPIPM, the average junction temperature should be limited to Tj(ave) ≤ 125°C (@ Tc ≤ 100°C).

## **CONTROL (PROTECTION) PART**

Symbol	Parameter	Condition	Ratings	Unit
VD	Control supply voltage	Applied between VP1-VNC, VN1-VNC	20	V
VDB	Control supply voltage	Applied between VUFB-U, VVFB-V, VWFB-W	20	V
Vin	Input voltage	Applied between UP, VP, WP, UN, VN, WN-VNC	-0.5~VD+0.5	>
VFO	Fault output supply voltage	Applied between Fo-VNC	-0.5~VD+0.5	V
IFO	Fault output current	Sink current at Fo terminal	1	mA
Vsc	Current sensing input voltage	Applied between CIN-VNC	-0.5~VD+0.5	V

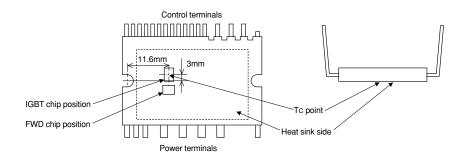


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#### **TOTAL SYSTEM**

Symbol	Parameter	Condition	Ratings	Unit
VCC(PROT)	Self protection supply voltage limit (short circuit protection capability)	$VD = 13.5 \sim 16.5 V$ , Inverter part $T_j = 125 °C$ , non-repetitive, less than 2μs	400	V
Tc	Module case operation temperature	(Note 2)	<b>−</b> 20~+100	°C
Tstg	Storage temperature		<b>−</b> 40~+125	°C
Viso	Isolation voltage	60Hz, Sinusoidal, 1 minute, Between pins and heat-sink plate	1500	Vrms

#### Note 2: To measurement point



#### THERMAL RESISTANCE

Cumbal	Darameter	Condition	Limits			Lloit
Symbol Parameter		Condition		Тур.	Max.	Unit
Rth(j-c)Q	Junction to case thermal	Inverter IGBT part (per 1/6 module)	_	_	3.0	°C/W
Rth(j-c)F	resistance (Note 3)			_	3.9	°C/W

Note 3: Grease with good thermal conductivity should be applied evenly with about +100μm~+200μm on the contacting surface of DIPIPM and heat-sink.

The contacting thermal resistance between DIPIPM case and heat sink (Rth(c-f)) is determined by the thickness and the thermal conductivity of the applied grease. For reference, Rth(c-f) (per 1/6 module) is about  $0.3^{\circ}$ C/W when the grease thickness is  $20\mu m$  and the thermal conductivity is  $1.0W/m \cdot k$ .

# **ELECTRICAL CHARACTERISTICS** ( $T_j = 25$ °C, unless otherwise noted) **INVERTER PART**

Cumbal	Davisanista	Condition -		Limits			Unit
Symbol	Parameter			Min.	Тур.	Max.	Unit
VCE(aat)	Collector-emitter saturation	VD = VDB = 15V	VD = VDB = 15V		1.70	2.20	.,
VCE(sat)	VCE(sat) voltage	VIN = 5V	IC = 15A, Tj = 125°C		1.80	2.30	V
VEC	FWD forward voltage	$T_j = 25^{\circ}C$ , $-I_C = 15A$ , $V_{IN} = 0V$			1.70	2.20	٧
ton		Vcc = 300V, VD = VDB = 15V		0.70	1.30	1.90	μs
trr					0.30	-	μs
tc(on)	Switching times	IC = 15A, Tj = 125°C, VIN	$IC = 15A$ , $T_j = 125^{\circ}C$ , $VIN = 0 \leftrightarrow 5V$		0.50	0.75	μs
toff		Inductive load (upper-lov	ver arm)		1.60	2.20	μs
tc(off)				I	0.50	0.80	μs
ICES	Collector-emitter cut-off	VCE = VCES	Tj = 25°C		_	1	mA
[	current	VCE = VCES	Tj = 125°C	_	_	10	IIIA



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## **CONTROL (PROTECTION) PART**

Symbol	Parameter	Condition				Limits		
Syllibol	Farameter		Condition		Min.	Тур.	Max.	Unit
		VD = VDB = 15V	Total	of VP1-VNC, VN1-VNC	_	_	2.80	mA
ID.	Circuit current	VIN = 5V VUFB		-U, Vvfb-V, Vwfb-W	_	_	0.55	mA
ם ו	Circuit current	VD = VDB = 15V	Total	of VP1-VNC, VN1-VNC	_	_	2.80	mA
		VIN = 0V	VUFB	-U, Vvfb-V, Vwfb-W	_	_	0.55	mA
VFOH	Fault output voltage	Vsc = 0V, Fo termi	Vsc = 0V, Fo terminal pull-up to 5V by $10k\Omega$		4.9	_	_	V
VFOL	Fault output voltage	Vsc = 1V, IFO = 1n	VSC = 1V, IFO = 1mA		_	_	0.95	V
VSC(ref)	Short circuit trip level	$T_j = 25^{\circ}C, VD = 15V$ (Note 4)		0.43	0.48	0.53	V	
lin	Input current	VIN = 5V		0.70	1.00	1.50	mA	
OTt	Over temperature protection	VD = 15V,		Trip level	100	120	140 °C	°C
OTrh	(Note 5)	At temperature of I	LVIC	Trip/reset hysteresis	_	10	_	
UVDBt				Trip level	10.0	_	12.0	V
UVDBr	Control supply under-voltage	T <sub>i</sub> ≤ 125°C		Reset level	10.5	_	12.5	V
UVDt	protection	1]≤ 125 C	Trip level	10.3	_	12.5	V	
UVDr				Reset level	10.8	_	13.0	V
tFO	Fault output pulse width		(Note 6)		20	_	_	μs
Vth(on)	ON threshold voltage		,		_	2.1	2.6	V
Vth(off)	OFF threshold voltage	Applied between UP, VP, WP, UN, VN, WN-VNC		0.8	1.3	_	V	
Vth(hys)	ON/OFF threshold hysteresis voltage			0.35	0.65	_	٧	

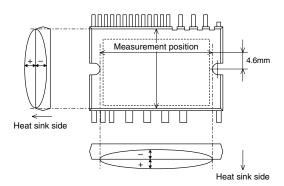
- Note 4: Short circuit protection is functioning only for the lower-arms. Please select the external shunt resistance such that the SC trip-level is less than 1.7 times of the current rating.
  - 5: Over temperature protection (OT) outputs fault signal, when the LVIC temperature exceeds OT trip temperature level (OTt). In that case if the heat sink comes off DIPIPM or fixed loosely, don't reuse that DIPIPM. (There is a possibility that junction temperature of power chips exceeded maximum Tj (150°C)).
  - **6:** Fault signal is asserted only corresponding to a SC, a UV or an OT failure at lower side, and the Fo pulse width is different for each failure modes. For SC failure, Fo output is with a fixed width of 20μsec(min), but for UV or OT failure, Fo output continuously during the whole UV or OT period, however, the minimum Fo pulse width is 20μsec(min) for very short UV or OT period less than 20μsec.

## **MECHANICAL CHARACTERISTICS AND RATINGS**

Doromotor	Condition		Limits			Unit
Parameter			Min.	Тур.	Max.	Unit
Mounting torque	Mounting screw : M3 (Note 7)	Recommended : 0.69 N·m	0.59	_	0.78	N·m
Weight			_	10	_	g
Heat-sink flatness		(Note 8)	-50	_	100	μm

Note 7: Plain washers (ISO 7089~7094) are recommended.

Note 8: Flatness measurement position





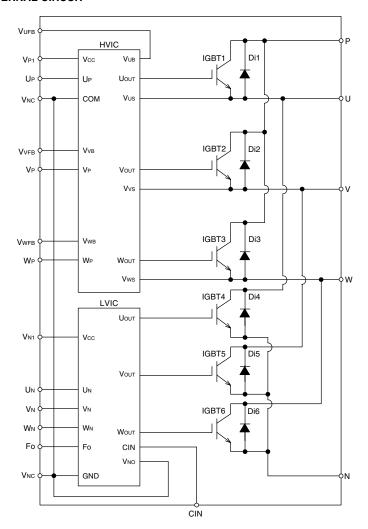
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#### RECOMMENDED OPERATION CONDITIONS

Commelle and	Davisantav	Condition		Limits			Unit
Symbol Parameter		Condition		Min.	Тур.	Max.	Unit
Vcc	Supply voltage	Applied between P-N			300	400	V
VD	Control supply voltage	Applied between VP1-VNC, VN1-VNC		13.5	15.0	16.5	V
VDB	Control supply voltage	Applied between VUFB-U, VVFB-V, VWFB-	W	13.0	15.0	18.5	V
$\Delta V$ D, $\Delta V$ DB	Control supply variation			-1	_	1	V/µs
tdead	Arm shoot-through blocking time	For each input signal, Tc ≤ 100°C		1.5	_	_	μs
fPWM	PWM input frequency	Tc ≤ 100°C, Tj ≤ 125°C		_	_	20	kHz
lo.	Allowable r.m.s. current	VCC = 300V, VD = VDB = 15V,	fPWM = 5kHz	1	_	7.5	Arms
lo	Allowable f.m.s. current	$\begin{array}{l} \text{P.F} = 0.8, \text{ sinusoidal PWM,} \\ \text{T}_{\text{j}} \leq 125^{\circ}\text{C}, \text{ Tc} \leq 100^{\circ}\text{C} \end{array} \tag{Note 9}$	fPWM = 15kHz	_	_	4.5	AIIIIS
PWIN(on)	Allowable minimum input			0.5	_	_	
PWIN(off)	pulse width		0.5	_	_	μs	
VNC	VNC variation	Between VNC-N (including surge)		-5.0	_	5.0	V

Note 9: The allowable r.m.s. current value depends on the actual application conditions.

Fig. 7 THE DIPIPM INTERNAL CIRCUIT





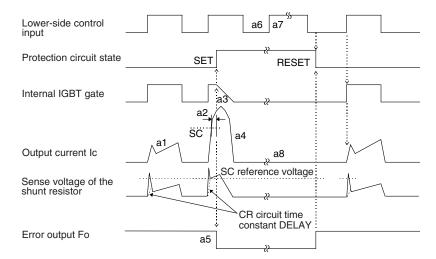
<sup>10:</sup> IPM might not make response if the input signal pulse width is less than the recommended minimum value.

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## Fig. 8 TIMING CHART OF THE DIPIPM PROTECTIVE FUNCTIONS

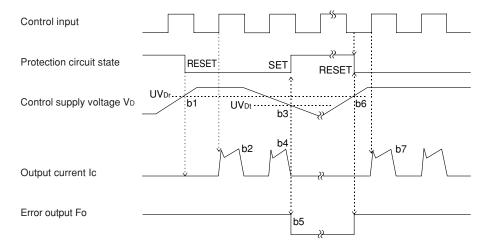
## [A] Short-Circuit Protection (Lower-side only with the external shunt resistor and CR filter)

- a1. Normal operation: IGBT ON and carrying current.
- a2. Short circuit detection (SC trigger).
- a3. IGBT gate hard interruption.
- a4. IGBT turns OFF.
- a5. Fo outputs (tFO(min) =  $20\mu$ s).
- a6. Input "L" : IGBT OFF.
- a7. Input "H": IGBT ON.
- a8. IGBT OFF in spite of input "H".



## [B] Under-Voltage Protection (Lower-side, UVD)

- b1. Control supply voltage rising: After the voltage level reaches UVDr, the circuits start to operate when next input is applied. b2. Normal operation: IGBT ON and carrying current.
- b3. Under voltage trip (UVDt).
- b4. IGBT OFF in spite of control input condition.
- b5. Fo outputs (trO  $\geq$  20 $\mu$ s and Fo outputs continuously during UV period). b6. Under voltage reset (UVDr). b7. Normal operation : IGBT ON and carrying current.

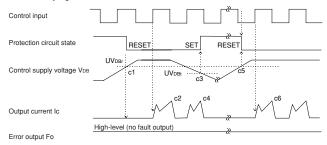




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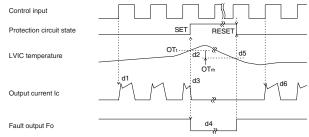
#### [C] Under-Voltage Protection (Upper-side, UVDB)

- c1. Control supply voltage rising: After the voltage level reaches UVDBr, the circuits start to operate when next input is applied.
- c2. Normal operation: IGBT ON and carrying current.
- c3. Under voltage trip (UVDBt).
- c4. IGBT OFF in spite of control input signal level, but there is no Fo signal outputs.
- c5. Under voltage reset (UVDBr).
- c6. Normal operation: IGBT ON and carrying current.

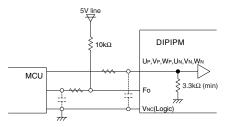


#### [D] Over Temperature Protection (Lower-side, OT)

- d1. Normal operation: IGBT ON and carrying current.
- d2. LVIC temperature exceeds over temperature trip level (OTt).
  d3. IGBT OFF in spite of control input condition.
- d4. Fo outputs during over temperature period, however, the minimum pulse width is  $20\mu s$ .
- d5. LVIC temperature becomes under over temperature reset level.
- d6. Circuits start to operate normally when next input is applied.



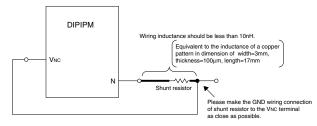
### Fig. 9 RECOMMENDED MCU I/O INTERFACE CIRCUIT



Note: The setting of RC coupling at each input (parts shown dotted) depends on the PWM control scheme and the wiring impedance of the printed circuit board.

The DIPIPM input section integrates a  $3.3k\Omega$  (min) pull-down resistor. Therefore, when using an external filtering resistor, pay attention to the turn-on threshold voltage.

## Fig. 10 WIRING CONNECTION OF SHUNT RESISTOR

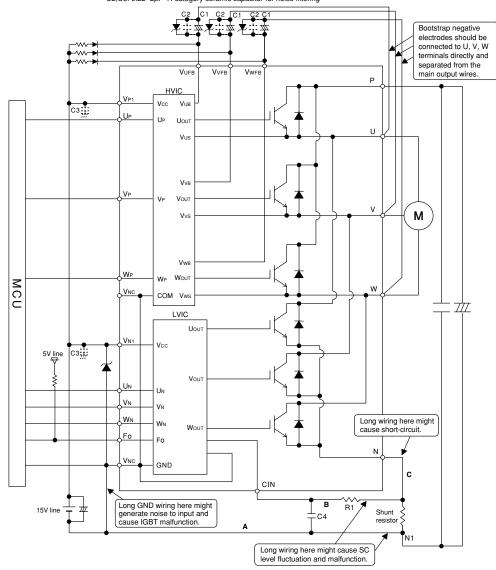




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### Fig. 11 AN EXAMPLE OF TYPICAL DIPIPM APPLICATION CIRCUIT

C1: Electrolytic capacitor with good temperature characteristics C2,C3: 0.22~2µF R-category ceramic capacitor for noise filtering



- Note 1 : Input drive is High-Active type. There is a 3.3kΩ(min.) pull-down resistor integrated in the IC input circuit. To prevent malfunction, the wiring of each input should be as short as possible. When using RC coupling circuit, make sure the input signal level meet the turn-on and turn-off threshold voltage.
  - 2 : Thanks to HVIC inside the module, direct coupling to MCU without any opto-coupler or transformer isolation is possible.
  - 3 : Fo output is open drain type. It should be pulled up to the positive side of a 5V power supply by a resistor of about 10kΩ.
  - : To prevent erroneous protection, the wiring of A, B, C should be as short as possible.
  - The time constant R1C4 of the protection circuit should be selected in the range of 1.5-2µs. SC interrupting time might vary with the wiring pattern. Tight tolerance, temp-compensated type is recommended for R1, C4.
     All capacitors should be mounted as close to the terminals of the DIPIPM as possible. (C1: good temperature, frequency character-
  - **6** : All capacitors should be mounted as close to the terminals of the DIPIPM as possible. (C1: good temperature, frequency characteristic electrolytic type, and C2, C3: good temperature, frequency and DC bias characteristic ceramic type are recommended.)
  - 7 :To prevent surge destruction, the wiring between the smoothing capacitor and the P, N1 terminals should be as short as possible. Generally a 0.1-0.22μF snubber between the P-N1 terminals is recommended.
  - 8 : Two VNC terminals (9 & 16 pin) are connected inside DIPIPM, please connect either one to the 15V power supply GND outside and leave another one open.
  - It is recommended to insert a Zener diode (24V/1W) between each pair of control supply terminals to prevent surge destruction.
  - 10: If control GND is connected to power GND by broad pattern, it may cause malfunction by power GND fluctuation. It is recommended to connect control GND and power GND at only a point.

